SiT8009B

High Frequency, Low Power Oscillator

The Smart Timing Choice™

Features

- Any frequency between 115 MHz and 137 MHz accurate to 6 decimal places
- 100% pin-to-pin drop-in replacement to quartz-based XO
- Excellent total frequency stability as low as ±20 ppm
- Operating temperature from -40°C to 85°C. For 125°C and/or -55°C options, refer to **SiT8919** and **SiT8921**
- Low power consumption of 4.9 mA typical at 1.8V
- Standby mode for longer battery life
- Fast startup time of 5 ms
- LVCMOS/HCMOS compatible output
- Industry-standard packages: 2.0 x 1.6, 2.5 x 2.0, 3.2 x 2.5, 5.0 x 3.2, 7.0 x 5.0 mm x mm
- Instant samples with Time Machine II and field programmable oscillators
- RoHS and REACH compliant, Pb-free, Halogen-free and Antimony-free
- **For AEC-Q100 oscillators, refer to SiT8924 and SiT8925**

Applications

- Ideal for GPON/GPON, network switches, routers. servers, embedded systems
- Ideal for Ethernet, PCI-E, DDR, etc.

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Electrical Specifications

Table 1. Electrical Characteristics

All Min and Max limits are specified over temperature and rated operating voltage with 15 pF output load unless otherwise stated. Typical values are at 25°C and nominal supply voltage.

Parameters	Symbol	Min.	Typ.	Max.	Unit	Condition
			Frequency Range			
Output Frequency Range	f	115	–	137	MHz	
			Frequency Stability and Aging			
Frequency Stability	F_stab	-20	–	+20	ppm	Inclusive of Initial tolerance at 25°C, 1st year aging at 25°C, and variations over operating temperature, rated power supply voltage and load.
		-25	–	+25	ppm	
		-50	–	+50	ppm	
			Operating Temperature Range			
Operating Temperature Range	T_use	-20	–	+70	°C	Extended Commercial
		-40	–	+85	°C	Industrial
			Supply Voltage and Current Consumption			
Supply Voltage	Vdd	1.62	1.8	1.98	V	Contact SiTime for 1.5V support
		2.25	2.5	2.75	V	
		2.52	2.8	3.08	V	
		2.7	3.0	3.3	V	
		2.97	3.3	3.63	V	
		2.25	–	3.63	V	
Current Consumption	Idd	–	6.2	7.5	mA	No load condition, f = 125 MHz, Vdd = 2.8V, 3.0V, 3.3V or 2.25 to 3.63V
		–	5.5	6.4	mA	No load condition, f = 125 MHz, Vdd = 2.5V
		–	4.9	5.6	mA	No load condition, f = 125 MHz, Vdd = 1.8V
OE Disable Current	I_OD	–	–	4.2	mA	Vdd = 2.5V to 3.3V, OE = GND, Output in high-Z state
		–	–	4.0	mA	Vdd = 1.8V, OE = GND, Output in high-Z state
Standby Current	I_std	–	2.6	4.3	µA	ST = GND, Vdd = 2.8V to 3.3V, Output is weakly pulled down
		–	1.4	2.5	µA	ST = GND, Vdd = 2.5V, Output is weakly pulled down
		–	0.6	1.3	µA	ST = GND, Vdd = 1.8V, Output is weakly pulled down
			LVCMOS Output Characteristics			
Duty Cycle	DC	45	–	55	%	All Vdds
Rise/Fall Time	Tr, Tf	–	1	2	ns	Vdd = 2.5V, 2.8V, 3.0V or 3.3V, 20% - 80%
		–	1.3	2.5	ns	Vdd =1.8V, 20% - 80%
		–	0.8	2	ns	Vdd = 2.25V - 3.63V, 20% - 80%
Output High Voltage	VOH	90%	–	–	Vdd	IOH = -4 mA (Vdd = 3.0V or 3.3V)
Output Low Voltage	VOL	–	–	10%	Vdd	IOL = 4 mA (Vdd = 3.0V or 3.3V)

Table 1. Electrical Characteristics (continued)

Parameters	Symbol	Min.	Typ.	Max.	Unit	Condition
Input Characteristics						
Input High Voltage	VIH	70%	–	–	Vdd	Pin 1, OE or ST
Input Low Voltage	VIL	–	–	30%	Vdd	Pin 1, OE or ST
Input Pull-up Impedance	Z_in	50	87	150	kΩ	Pin 1, OE logic high or logic low, or ST logic high
		2	–	–	MΩ	Pin 1, ST logic low
Startup and Resume Timing						
Startup Time	T_start	–	–	5	ms	Measured from the time Vdd reaches its rated minimum value
Enable/Disable Time	T_oe	–	–	122	ns	f = 137 MHz. For other frequencies, T_oe = 100 ns + 3 * cycles
Resume Time	T_resume	–	–	5	ms	Measured from the time ST pin crosses 50% threshold
Jitter						
RMS Period Jitter	T_jitt	–	1.9	3	ps	f = 125 MHz, Vdd = 2.5V, 2.8V, 3.0V or 3.3V
		–	1.8	4	ps	f = 125 MHz, Vdd = 1.8V
Peak-to-peak Period Jitter	T_pk	–	12	25	ps	f = 125 MHz, Vdd = 2.5V, 2.8V, 3.0V or 3.3V
		–	14	30	ps	f = 125 MHz, Vdd = 1.8V
RMS Phase Jitter (random)	T_phj	–	0.5	0.9	ps	Integration bandwidth = 900 kHz to 7.5 MHz
		–	1.3	2	ps	Integration bandwidth = 12 kHz to 20 MHz

Table 2. Pin Description

Pin	Symbol	Functionality	
1	OE/ $\overline{ST}$/NC	Output Enable	H[1]: specified frequency output L: output is high impedance. Only output driver is disabled.
		Standby	H[1]: specified frequency output L: output is low (weak pull down). Device goes to sleep mode. Supply current reduces to I_std.
		No Connect	Any voltage between 0 and Vdd or Open[1]: Specified frequency output. Pin 1 has no function.
2	GND	Power	Electrical ground
3	OUT	Output	Oscillator output
4	VDD	Power	Power supply voltage[2]

Notes:

1. In OE or $\overline{ST}$ mode, a pull-up resistor of 10 kΩ or less is recommended if pin 1 is not externally driven. If pin 1 needs to be left floating, use the NC option.
2. A capacitor of value 0.1 µF or higher between Vdd and GND is required.

Top View

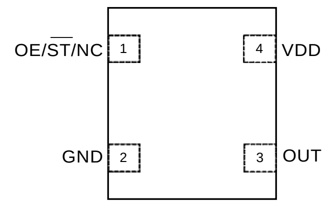


Figure 1. Pin Assignments

Table 3. Absolute Maximum Limits

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Storage Temperature	-65	150	°C
Vdd	-0.5	4	V
Electrostatic Discharge	–	2000	V
Soldering Temperature (follow standard Pb free soldering guidelines)	–	260	°C
Junction Temperature[3]	–	150	°C

Note:

3. Exceeding this temperature for extended period of time may damage the device.

Table 4. Thermal Consideration[4]

Package	θJA, 4 Layer Board (°C/W)	θJA, 2 Layer Board (°C/W)	θJC, Bottom (°C/W)
7050	142	273	30
5032	97	199	24
3225	109	212	27
2520	117	222	26
2016	152	252	36

Note:

4. Refer to JESD51 for θJA and θJC definitions, and reference layout used to determine the θJA and θJC values in the above table.

Table 5. Maximum Operating Junction Temperature[5]

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
70°C	80°C
85°C	95°C

Note:

5. Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.

Table 6. Environmental Compliance

Parameter	Condition/Test Method
Mechanical Shock	**MIL-STD-883F, Method 2002**
Mechanical Vibration	**MIL-STD-883F, Method 2007**
Temperature Cycle	**JESD22, Method A104**
Solderability	**MIL-STD-883F, Method 2003**
Moisture Sensitivity Level	**MSL1 @ 260°C**

Test Circuit and Waveform[6]

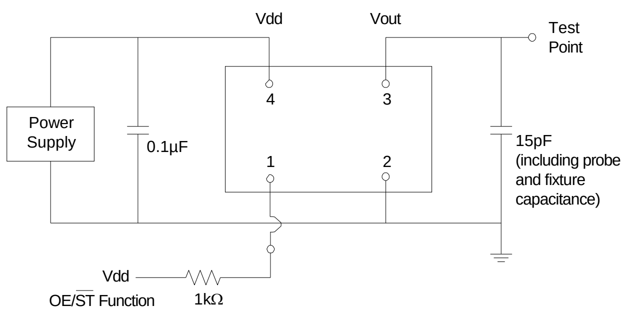


Figure 2. Test Circuit

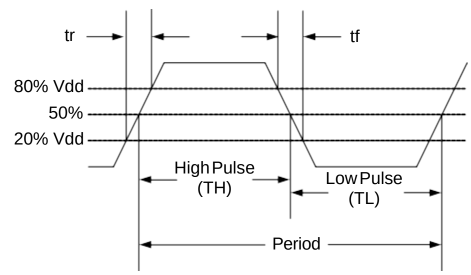
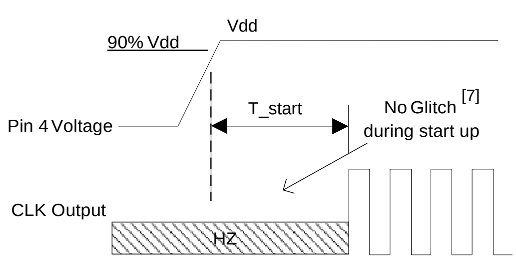


Figure 3. Waveform

Note:

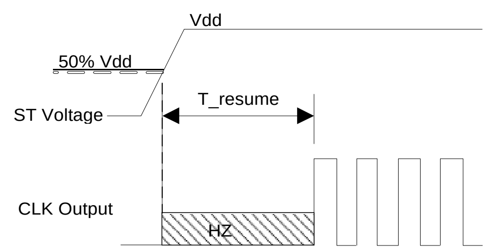
6. Duty Cycle is computed as Duty Cycle = TH/Period.

Timing Diagrams



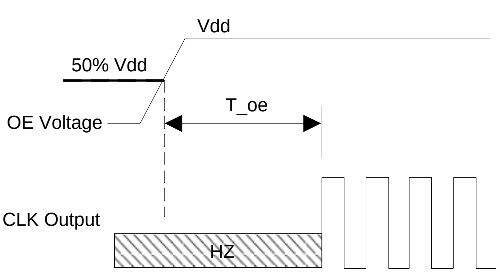
T_start: Time to start from power-off

Figure 4. Startup Timing (OE/ST Mode)



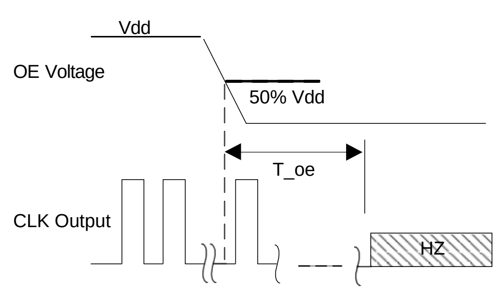
T_resume: Time to resume from ST

Figure 5. Standby Resume Timing (ST Mode Only)



T_oe: Time to re-enable the clock output

Figure 6. OE Enable Timing (OE Mode Only)



T_oe: Time to put the output in High Z mode

Figure 7. OE Disable Timing (OE Mode Only)

Note:

7. SiT8009 has “no runt” pulses and “no glitch” output during startup or resume.

Performance Plots[8]

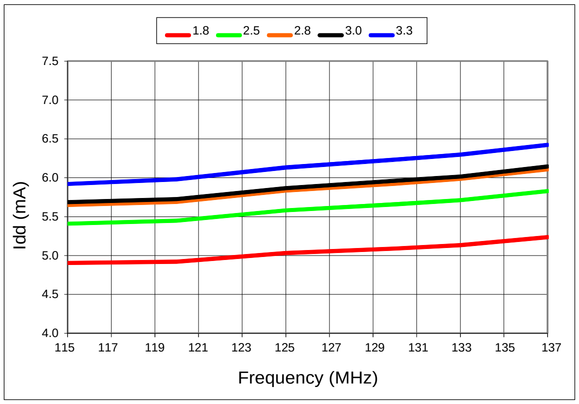


Figure 8. Idd vs Frequency

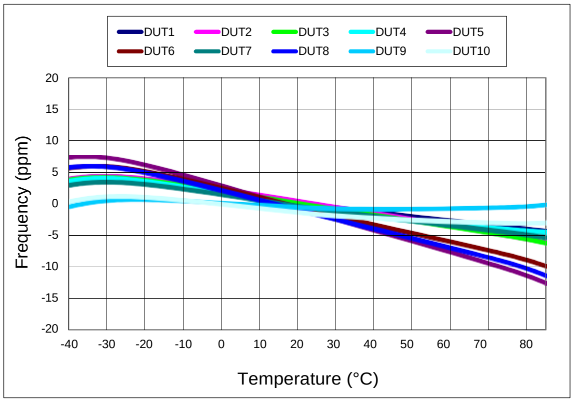


Figure 9. Frequency vs Temperature, 1.8V

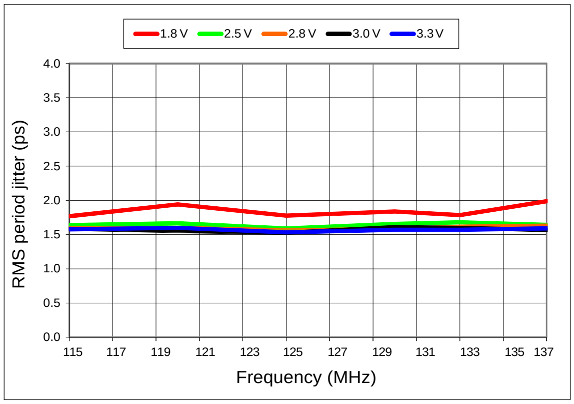


Figure 10. RMS Period Jitter vs Frequency

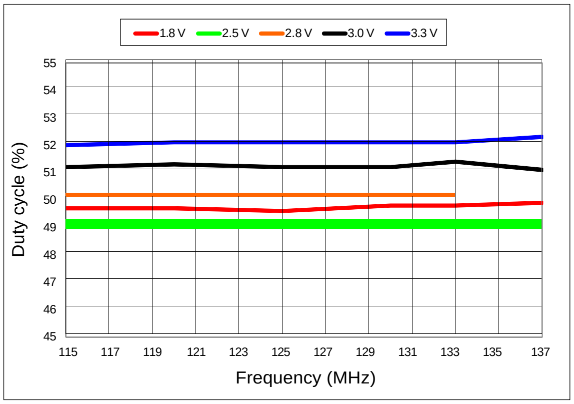


Figure 11. Duty Cycle vs Frequency

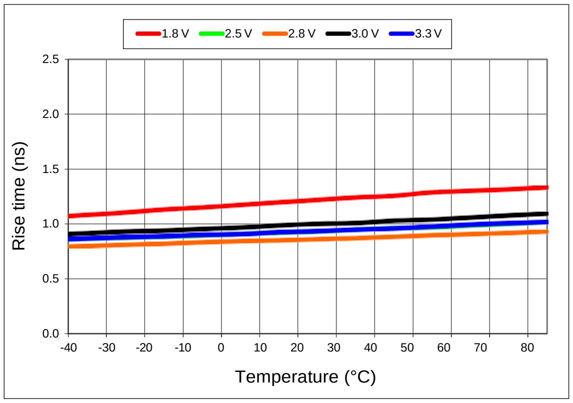


Figure 12. 20%-80% Rise Time vs Temperature

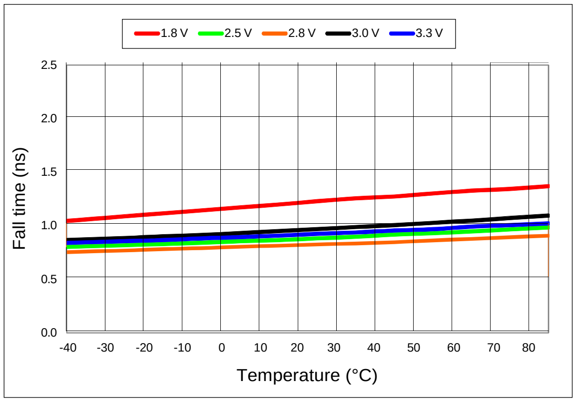


Figure 13. 20%-80% Fall Time vs Temperature

Performance Plots[8]

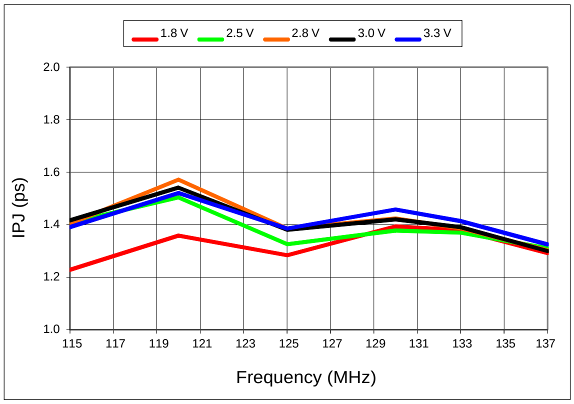


Figure 14. RMS Integrated Phase Jitter Random (12 kHz to 20 MHz) vs Frequency[9]

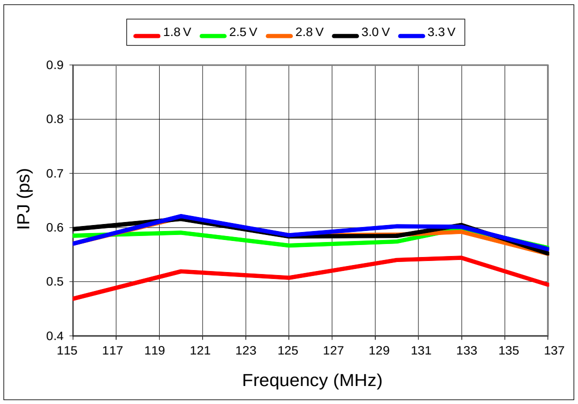


Figure 15. RMS Integrated Phase Jitter Random (900 kHz to 20 MHz) vs Frequency[9]

Notes:

8. All plots are measured with 15 pF load at room temperature, unless otherwise stated.
9. Phase noise plots are measured with Agilent E5052B signal source analyzer.

Programmable Drive Strength

The SiT8009 includes a programmable drive strength feature to provide a simple, flexible tool to optimize the clock rise/fall time for specific applications. Benefits from the programmable drive strength feature are:

- Improves system radiated electromagnetic interference (EMI) by slowing down the clock rise/fall time
- Improves the downstream clock receiver's (RX) jitter by decreasing (speeding up) the clock rise/fall time.
- Ability to drive large capacitive loads while maintaining full swing with sharp edge rates.

For more detailed information about rise/fall time control and drive strength selection, see the SiTime Applications Note section; http://www.sitime.com/support/application-notes.

EMI Reduction by Slowing Rise/Fall Time

Figure 16 shows the harmonic power reduction as the rise/fall times are increased (slowed down). The rise/fall times are expressed as a ratio of the clock period. For the ratio of 0.05, the signal is very close to a square wave. For the ratio of 0.45, the rise/fall times are very close to near-triangular waveform. These results, for example, show that the 11th clock harmonic can be reduced by 35 dB if the rise/fall edge is increased from 5% of the period to 45% of the period.

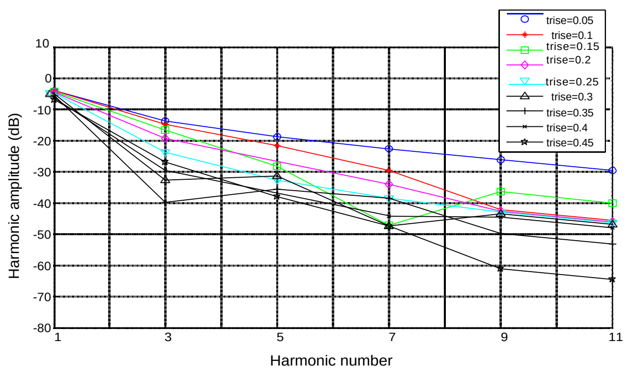


Figure 16. Harmonic EMI reduction as a Function of Slower Rise/Fall Time

Jitter Reduction with Faster Rise/Fall Time

Power supply noise can be a source of jitter for the downstream chipset. One way to reduce this jitter is to speed up the rise/fall time of the input clock. Some chipsets may also require faster rise/fall time in order to reduce their sensitivity to this type of jitter. Refer to the Rise/Fall Time Tables (Table 7 to Table 11) to determine the proper drive strength.

High Output Load Capability

The rise/fall time of the input clock varies as a function of the actual capacitive load the clock drives. At any given drive strength, the rise/fall time becomes slower as the output load increases. As an example, for a 3.3V SiT8009 device with default drive strength setting, the typical rise/fall time is 0.46 ns for 5 pF output load. The typical rise/fall time slows down to 1 ns when the output load increases to 15 pF. One can choose to speed up the rise/fall time to 0.72 ns by then increasing the driven strength setting on the SiT8009 to "F."

The SiT8009 can support up to 30 pF or higher in maximum capacitive loads with up to 3 additional drive strength settings. Refer to the Rise/Fall Time Tables (Table 7 to 11) to determine the proper drive strength for the desired combination of output load vs. rise/fall time

SiT8009 Drive Strength Selection

Tables 7 through 11 define the rise/fall time for a given capacitive load and supply voltage.

1. Select the table that matches the SiT8009 nominal supply voltage (1.8V, 2.5V, 2.8V, 3.0V, 3.3V).
2. Select the capacitive load column that matches the application requirement (5 pF to 30 pF)
3. Under the capacitive load column, select the desired rise/fall times.
4. The left-most column represents the part number code for the corresponding drive strength.
5. Add the drive strength code to the part number for ordering purposes.

Calculating Maximum Frequency

Based on the rise and fall time data given in Tables 7 through 11, the maximum frequency the oscillator can operate with guaranteed full swing of the output voltage over temperature as follows:

$$\text{Max Frequency} = \frac{1}{5 \times T_{rf\_20/80}}$$

where Trf_20/80 is the typical value for 20%-80% rise/fall time.

Example 1

Calculate f_{MAX} for the following condition:

- Vdd = 3.3V (Table 11)
- Capacitive Load: 30 pF
- Desired Tr/f time = 1.46 ns (rise/fall time part number code = U)

Part number for the above example:

SiT8009BI**U**12-33E-136.986300

Drive strength code is inserted here. Default setting is "-"

Rise/Fall Time (20% to 80%) vs C_{LOAD} Tables

Table 7. Vdd = 1.8V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)			
Drive Strength \ C_{LOAD}	5 pF	15 pF	30 pF
T	0.93	n/a	n/a
E	0.78	n/a	n/a
U	0.70	1.48	n/a
F or "-": default	0.65	1.30	n/a

Table 8. Vdd = 2.5V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)			
Drive Strength \ C_{LOAD}	5 pF	15 pF	30 pF
R	1.45	n/a	n/a
B	1.09	n/a	n/a
T	0.62	1.28	n/a
E	0.54	1.00	n/a
U or "-": default	0.43	0.96	n/a
F	0.34	0.88	n/a

Table 9. Vdd = 2.8V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)			
Drive Strength \ C_{LOAD}	5 pF	15 pF	30 pF
R	1.29	n/a	n/a
B	0.97	n/a	n/a
T	0.55	1.12	n/a
E	0.44	1.00	n/a
U or "-": default	0.34	0.88	n/a
F	0.29	0.81	1.48

Table 10. Vdd = 3.0V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)			
Drive Strength \ C_{LOAD}	5 pF	15 pF	30 pF
R	1.22	n/a	n/a
B	0.89	n/a	n/a
T or "-": default	0.51	1.00	n/a
E	0.38	0.92	n/a
U	0.30	0.83	n/a
F	0.27	0.76	1.39

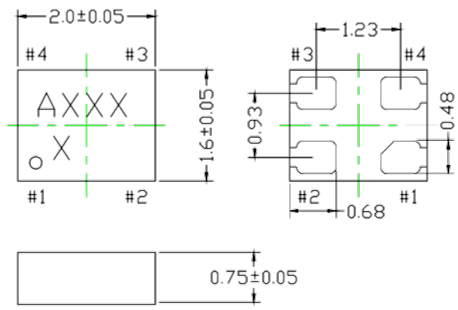
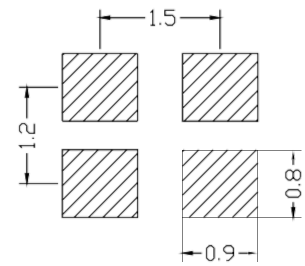
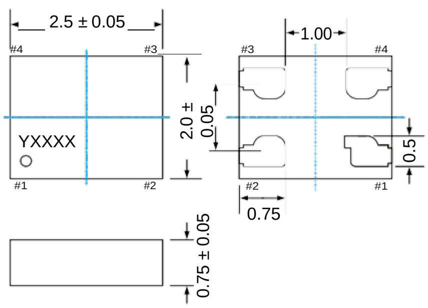
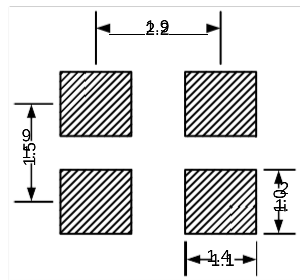
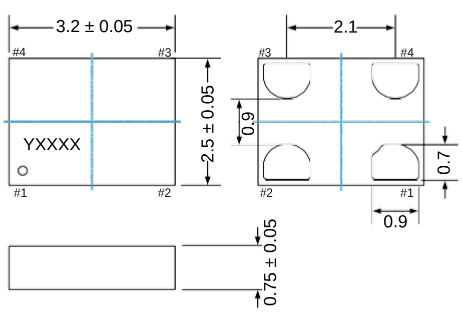
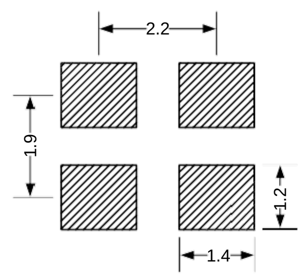
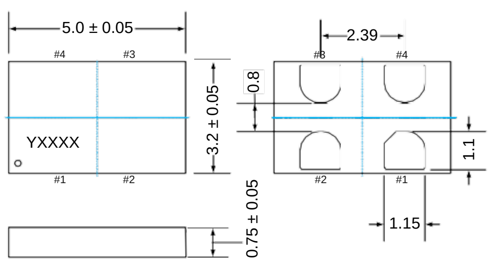
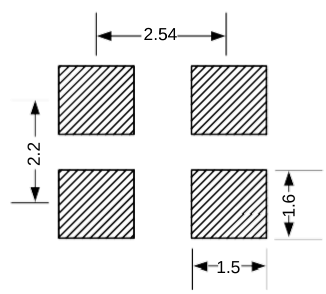
Table 11. Vdd = 3.3V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)			
Drive Strength \ C_{LOAD}	5 pF	15 pF	30 pF
R	1.16	n/a	n/a
B	0.81	n/a	n/a
T or "-": default	0.46	1.00	n/a
E	0.33	0.87	n/a
U	0.28	0.79	1.46
F	0.25	0.72	1.31

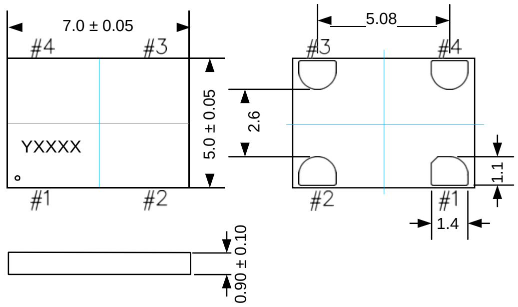
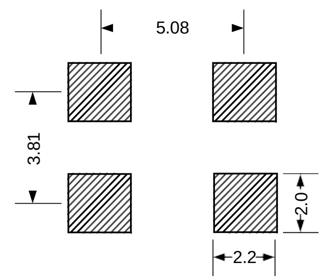
Note:

10. "n/a" in Table 7 to Table 11 indicates that the resulting rise/fall time from the respective combination of the drive strength and output load does not provide rail-to-rail swing and is not available.

Dimensions and Patterns

Package Size – Dimensions (Unit: mm)[11]	Recommended Land Pattern (Unit: mm)[12]
2.0 x 1.6 x 0.75 mm 	
2.5 x 2.0 x 0.75 mm 	
3.2 x 2.5 x 0.75 mm 	
5.0 x 3.2 x 0.75 mm 	

Dimensions and Patterns

Package Size – Dimensions (Unit: mm)[11]	Recommended Land Pattern (Unit: mm)[12]
7.0 x 5.0 x 0.90 mm 	

Notes:

11. Top marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.
12. A capacitor of value 0.1 µF or higher between Vdd and GND is required.

Ordering Information

The Part No. Guide is for reference only. To customize and build an exact part number, use the SiTime Part Number Generator.

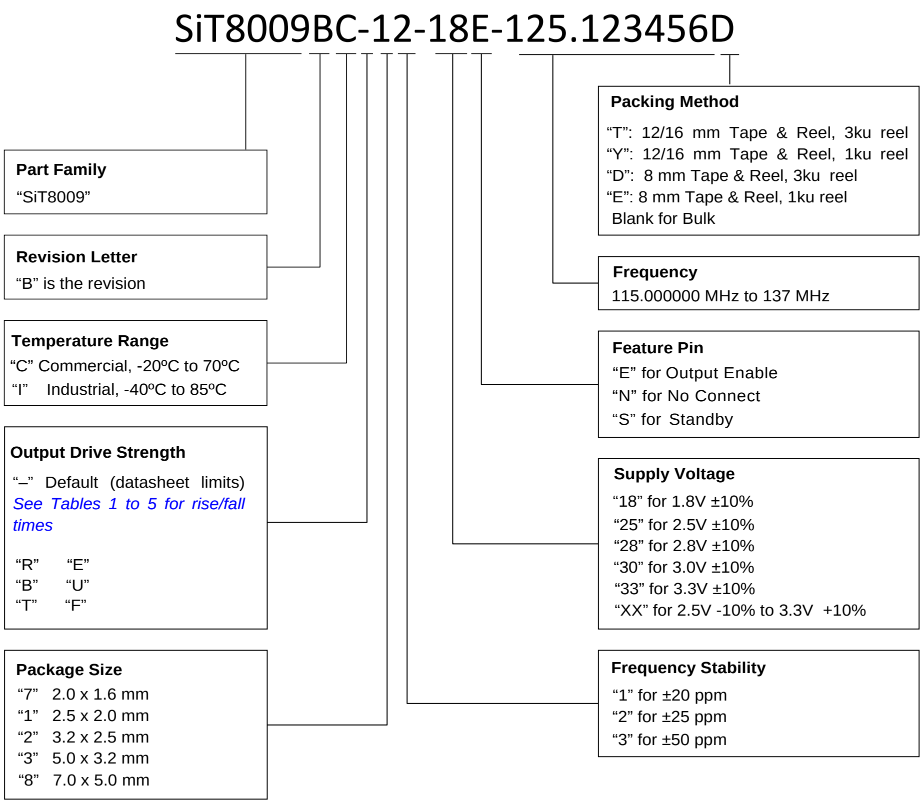


Table 13. Ordering Codes for Supported Tape & Reel Packing Method

Device Size (mm x mm)	16 mm T&R (3ku)	16 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	8 mm T&R (3ku)	8 mm T&R (1ku)
2.0 x 1.6	–	–	–	–	D	E
2.5 x 2.0	–	–	–	–	D	E
3.2 x 2.5	–	–	–	–	D	E
5.0 x 3.2	–	–	T	Y	–	–
7.0 x 5.0	T	Y	–	–	–	–

Silicon MEMS Outperforms Quartz

SiTime
The Smart Timing Choice™

Best Reliability

Silicon is inherently more reliable than quartz. Unlike quartz suppliers, SiTime has in-house MEMS and analog CMOS expertise, which allows SiTime to develop the most reliable products. Figure 1 shows a comparison with quartz technology.

Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal™ process, which eliminates foreign particles and improves long term aging and reliability
- World-class MEMS and CMOS design expertise

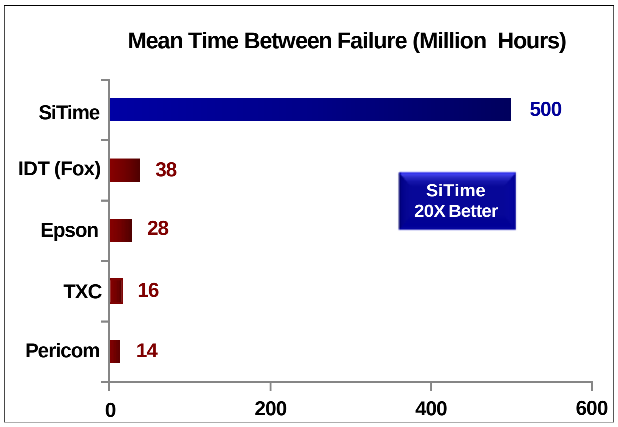


Figure 1. Reliability Comparison[1]

Best Electro Magnetic Susceptibility (EMS)

SiTime's oscillators in plastic packages are up to 54 times more immune to external electromagnetic fields than quartz oscillators as shown in Figure 3.

Why is SiTime Best in Class:

- Internal differential architecture for best common mode noise rejection
- Electrostatically driven MEMS resonator is more immune to EMS

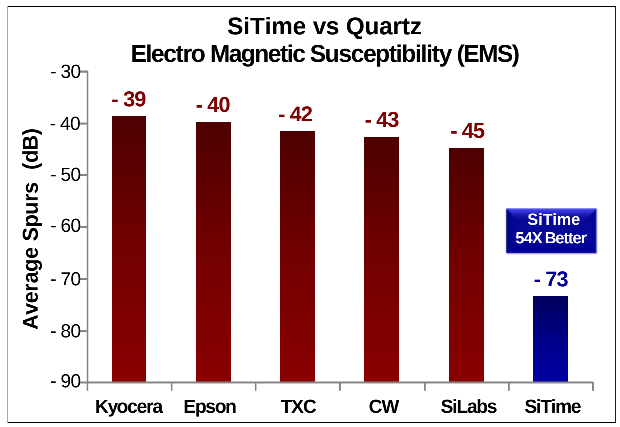


Figure 3. Electro Magnetic Susceptibility (EMS)[3]

Best Aging

Unlike quartz, MEMS oscillators have excellent long term aging performance which is why every new SiTime product specifies 10-year aging. A comparison is shown in Figure 2.

Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal process, which eliminates foreign particles and improves long term aging and reliability
- Inherently better immunity of electrostatically driven MEMS resonator

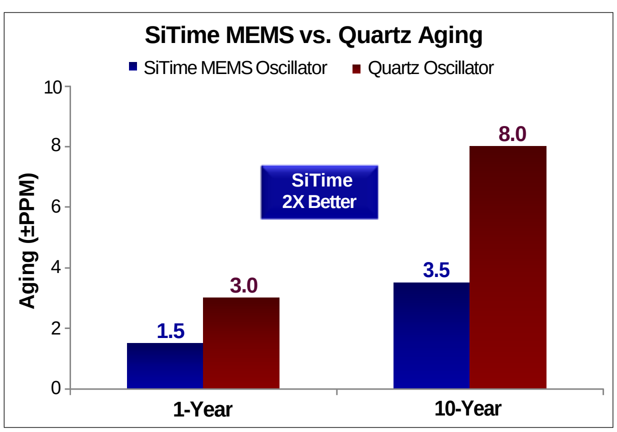


Figure 2. Aging Comparison[2]

Best Power Supply Noise Rejection

SiTime's MEMS oscillators are more resilient against noise on the power supply. A comparison is shown in Figure 4.

Why is SiTime Best in Class:

- On-chip regulators and internal differential architecture for common mode noise rejection
- Best analog CMOS design expertise

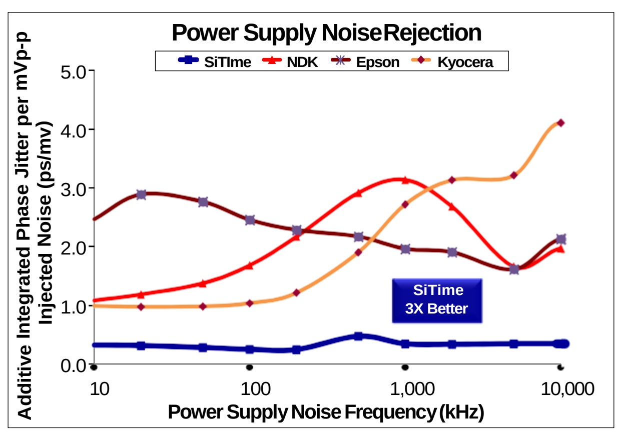


Figure 4. Power Supply Noise Rejection[4]

Silicon MEMS Outperforms Quartz

The Smart Timing Choice™

Best Vibration Robustness

High-vibration environments are all around us. All electronics, from handheld devices to enterprise servers and storage systems are subject to vibration. Figure 5 shows a comparison of vibration robustness.

Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than quartz
- Center-anchored MEMS resonator is the most robust design

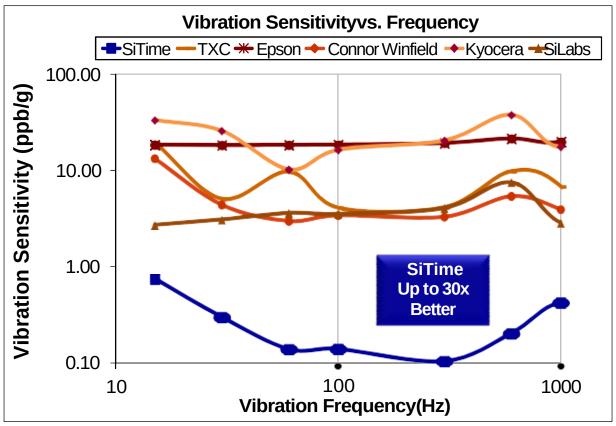


Figure 5. Vibration Robustness[5]

Best Shock Robustness

SiTime's oscillators can withstand at least 50,000 *g* shock. They all maintain their electrical performance in operation during shock events. A comparison with quartz devices is shown in Figure 6.

Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than quartz
- Center-anchored MEMS resonator is the most robust design

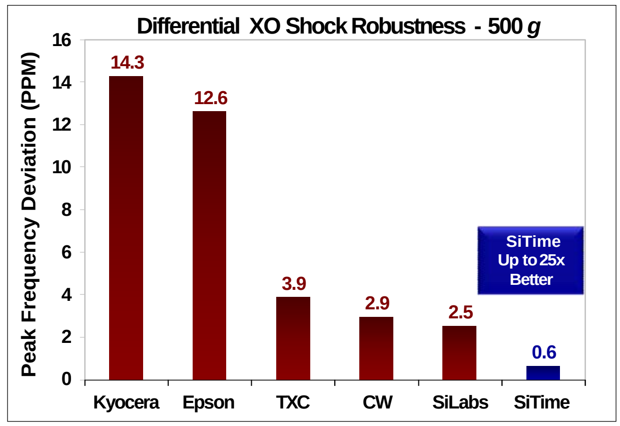


Figure 6. Shock Robustness[6]

Notes:

1. Data Source: Reliability documents of named companies.
2. Data source: SiTime and quartz oscillator devices datasheets.
3. Test conditions for Electro Magnetic Susceptibility (EMS):
   - According to IEC EN61000-4.3 (Electromagnetic compatibility standard)
   - Field strength: 3V/m
   - Radiated signal modulation: AM 1 kHz at 80% depth
   - Carrier frequency scan: 80 MHz – 1 GHz in 1% steps
   - Antenna polarization: Vertical
   - DUT position: Center aligned to antenna

   Devices used in this test:
   SiTime, SiT9120AC-1D2-33E156.250000 - MEMS based - 156.25 MHz
   Epson, EG-2102CA 156.2500M-PHPAL3 - SAW based - 156.25 MHz
   TXC, BB-156.250MBE-T - 3rd Overtone quartz based - 156.25 MHz
   Kyocera, KC7050T156.250P30E00 - SAW based - 156.25 MHz
   Connor Winfield (CW), P123-156.25M - 3rd overtone quartz based - 156.25 MHz
   SiLabs, Si590AB-BDG - 3rd overtone quartz based - 156.25 MHz
4. 50 mV pk-pk Sinusoidal voltage.

   Devices used in this test:
   SiTime, SiT8208AI-33-33E-25.000000, MEMS based - 25 MHz
   NDK, NZ2523SB-25.6M - quartz based - 25.6 MHz
   Kyocera, KC2016B25M0C1GE00 - quartz based - 25 MHz
   Epson, SG-310SCF-25M0-MB3 - quartz based - 25 MHz
5. **Devices used in this test:** same as EMS test stated in Note 3.
6. Test conditions for shock test:
   - MIL-STD-883F Method 2002
   - Condition A: half sine wave shock pulse, 500-g, 1ms
   - Continuous frequency measurement in 100 µs gate time for 10 seconds

   Devices used in this test: same as EMS test stated in Note 3